## **RESPONSE UNDER 37 CFR §1.116** EXPEDITED PROCEDURE **TECHNOLOGY CENTER ART JUNIT 2811**

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Tomoyoshi KUSHIDA

CENTER OFFICE OF CENTER OFFICE OF CENTER OF CE

Application No.: 09/435,766

Examiner:

S. Loke

Filed: November 8, 1999

Docket No.:

104361

For:

SEMICONDUCTOR DEVICE

## AMENDMENT AFTER FINAL REJECTION UNDER 37 CFR §1.116

Director of the U.S. Patent and Trademark Office Washington, D.C. 20231

Sir:

In reply to the Office Action mailed January 18, 2002, please amend the aboveidentified application as follows:

## IN THE CLAIMS:

Please replace claims 1, 4, 12, 22-23, 26 and 28-30 as follows:

(Three Times Amended) A bipolar semiconductor device comprising: 1.

a drain electrode;

a drain region having a first conductive type and disposed on the drain

electrode;

a drift region having a second conductive type different from the first conductive type of the drain region and disposed on the drain region;